查询"MT3S06FS"供应商SHIBA Transistor Silicon NPN Epitaxial Planar Type

MT3S06FS

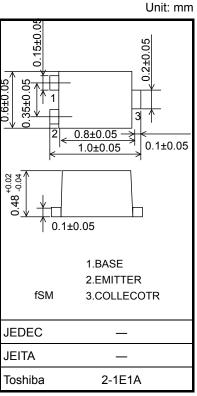
VHF~UHF Band Low-Noise Amplifier Applications VHF~UHF Band Buffer Applications

- · Superior performance in buffer applications
- · Superior noise characteristics

: NF = 1.7 dB, $|S_{21e}|^2$ = 8.5 dB (f = 2 GHz)

Absolute Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	10	V
Collector-emitter voltage	V _{CEO}	5	V
Emitter-base voltage	V _{EBO}	1.5	٧
Collector current	IC	15	mA
Base current	ΙΒ	7	mW
Collector power dissipation	P _C (Note)	85	mW
Junction temperature	Tj	125	°C
Storage temperature range	T _{stg}	-55~125	°C



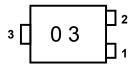
Weight: 0.0006 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note: 10mm² ×0.8 mm(t), mounted on a glass-epoxy printed circuit board.

Marking



MicroWave Characteristics (Ta = 25°C)

Characteristic	Symbol	Condition	Min	Тур.	Max	Unit
Transition frequency	f _T	$V_{CE} = 3 \text{ V}, I_{C} = 5 \text{ mA}$	7	10	_	GHz
Insertion gain	S _{21e} ² (1)	$V_{CE} = 1 \text{ V}, I_{C} = 5 \text{ mA}, f = 2 \text{ GHz}$	_	8.5	_	· dB
	S _{21e} ² (2)	$V_{CE} = 3 \text{ V}, I_{C} = 7 \text{ mA}, f = 2 \text{ GHz}$	7	9.5	_	
Noise figure	NF (1)	$V_{CE} = 1 \text{ V}, I_C = 3 \text{ mA}, f = 2 \text{ GHz}$	_	1.7	3	dB

Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Condition	Min	Тур.	Max	Unit
Collector cutoff current	I _{CBO}	$V_{CB} = 5 \text{ V}, I_{E} = 0$	_	_	0.1	μΑ
Emitter cutoff current	I _{EBO}	V _{EB} = 1 V, I _C = 0	_	_	1	μΑ
DC current gain	h _{FE}	V _{CE} = 1 V, I _C = 5 mA	70	_	140	
Reverse transfer capacitance	C _{re}	V _{CB} = 1 V, I _E = 0, f = 1 MHz(Note)	_	0.25	0.5	pF

Note: C_{re} is measured with a three-terminal method using a capacitance bridge.

Caution

This device is sensitive to electrostatic discharge. Ensure that tools and equipment are sufficiently grounded before handling. When handling individual devices (which are not yet mounted on a circuit board), ensure that the environment is protected against electrostatic discharge. Operators should wear antistatic clothing, and containers and other objects that come into direct contact with devices should be made of antistatic materials.

查询"MT3S06FS"供应商

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20070701-EN GENERAL

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